

N-channel 60 V 2 mΩ standard level MOSFET in D2PAK Rev. 2 — 29 February 2012 Product dat

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

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- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data			_		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> _	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	306	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	-	1.66	2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 13</u> ;see <u>Figure 12</u>	-	2.66	3.1	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 75 A; V_{DS} = 30 V;	-	32	-	nC
Q _{G(tot)}	total gate charge	see Figure 14;see Figure 15	-	137	-	nC
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 120 \text{ A}; \\ V_{sup} \leq 60 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \text{ Unclamped} $	-	-	913	mJ

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R7-60BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

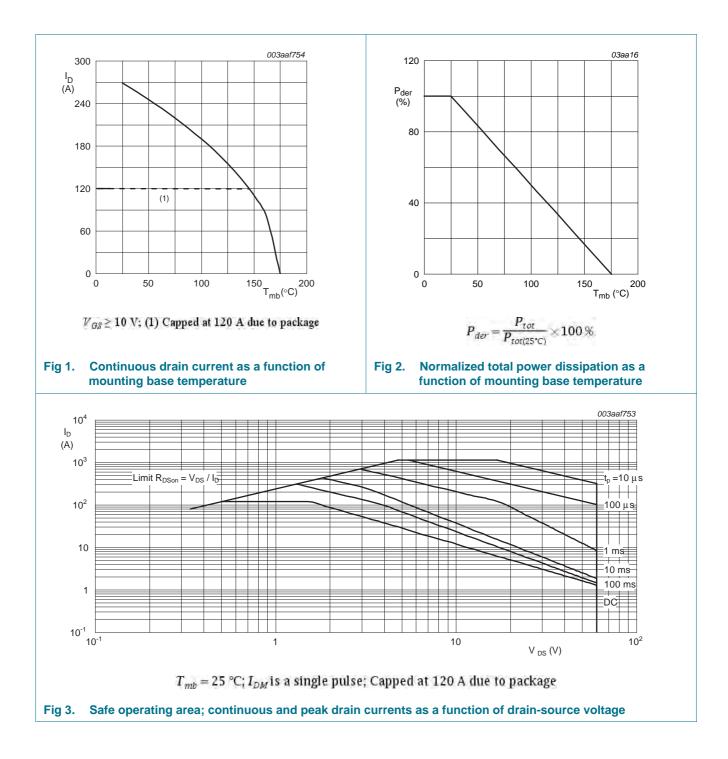
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	60	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	120	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	1076	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	306	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-di	rain diode				
ls	source current	T _{mb} = 25 °C	<u>[1]</u> -	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	1076	А
Avalanch	e ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω ; Unclamped	-	913	mJ

[1] Continuous current is limited by package.

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PSMN1R7-60BS

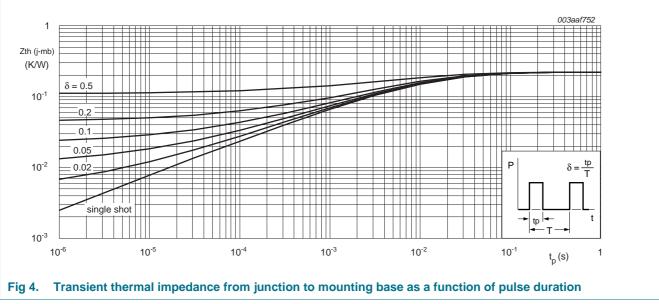
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	I_D = 250 $\mu A; V_{GS}$ = 0 V; T_j = -55 °C	54	-	-	V
	breakdown voltage	I_D = 250 $\mu A; \ V_{GS}$ = 0 V; T_j = 25 °C	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	10	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	-	1.66	2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	3.82	4.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 13</u> ; see <u>Figure 12</u>	-	2.66	3.1	mΩ
R _G	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I_D = 75 A; V_{DS} = 30 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	137	-	nC
		$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	129	-	nC
Q _{GS}	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	48	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	29	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	19	-	nC
Q _{GD}	gate-drain charge		-	32	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 30 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	5.7	-	V
C _{iss}	input capacitance	V _{DS} = 30 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C;	-	9997	-	pF
C _{oss}	output capacitance	see Figure 16	-	1210	-	pF
C _{rss}	reverse transfer capacitance		-	594	-	рF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 0.4 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	42	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ I_D = 75 \ A$	-	56	-	ns
t _{d(off)}	turn-off delay time		-	115	-	ns
t _f	fall time		-	49	-	ns

Symbol

PSMN1R7-60BS

Тур

Max Unit

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Min

ource-dra	ain diode							
SD	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; \text{ T}$ see <u>Figure 17</u>	_j = 25 °C;	-	- 0.	.8	1.2	V
r	reverse recovery time	I _S = 25 A; dI _S /dt = -100 V _{DS} = 30 V) A/ μ s; V _{GS} = 0 V;		- 57	7	-	ns
Q _r recovered charge		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ V}$ $V_{DS} = 30 \text{ V}$) A/µs; V _{GS} = 0 V;	-	- 80	0	-	nC
250 g _{fs} (S) 200		003aaf742	80 I _D (A) 60			003	Baaf743	
100			40					
50			20	T _j = 175 °C		= 25 °	∘C	
-								
0	$T_{j} = 25 \text{ °C}; V_{DS} =$	90 _{I_D(A)} 120 30V	0	2	4	V _{GS} (V) 6	
0 Fig 5. F		30V e as a function of es	0 Fig 6. Transfe	2 r characterist n of gate-sour	ics: drai	n cu ge; t	irrent a	
0 Fig 5. F	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductanc	30V e as a function of es	0 Fig 6. Transfe	r characterist	ics: drai	n cu ge; t	arrent (aypical)	
⁶ Fig 5. Fi du 10 ⁵	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductanc	30V e as a function of es	0 Fig 6. Transfer function	r characterist of gate-sour	ics: drai	n cu ge; t	irrent a	
¹⁰⁵ C (PF)	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductanc	30V e as a function of es	0 Fig 6. Transfer function	r characterist of gate-sour	ics: drai	n cu ge; t	3aad674	
¹⁰⁵ C (pF) 10 ⁴	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductance rain current; typical valu	30V e as a function of es	0 Fig 6. Transfe function	r characterist of gate-sour	ics: drai	n cu ge; t	3aad674	
Fig 5. Fi du 10 ⁵ C (pF) 10 ⁴ 10 ³	$T_j = 25 \text{ °C}; V_{DS} =$ orward transconductance rain current; typical valu	30V e as a function of b 003aaf746 C_{iss} C_{rss}	0 Fig 6. Transfe function (A) 150 100 50 0	r characterist	ve	n cu ge; t 003	<pre>v) irrent a typical 3aad674 4.5 = 4 </pre>	

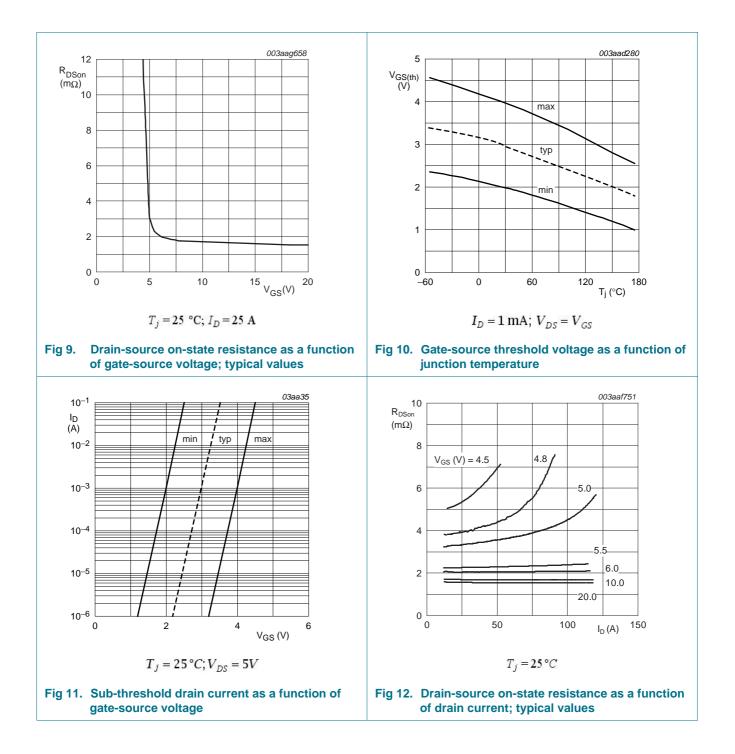
Characteristics ... continued Table 6. Parameter

Conditions

Product data sheet

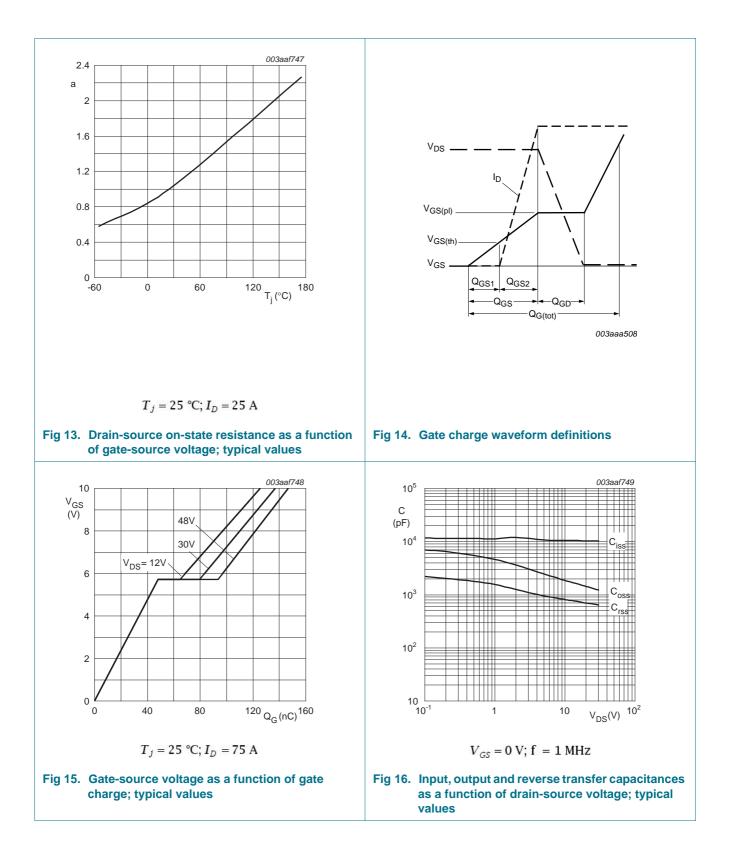
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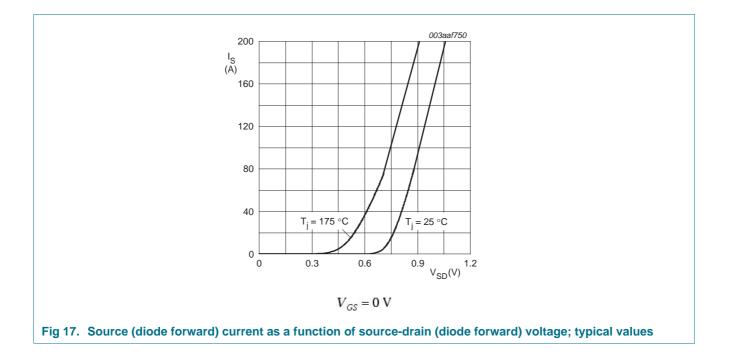
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7. Package outline

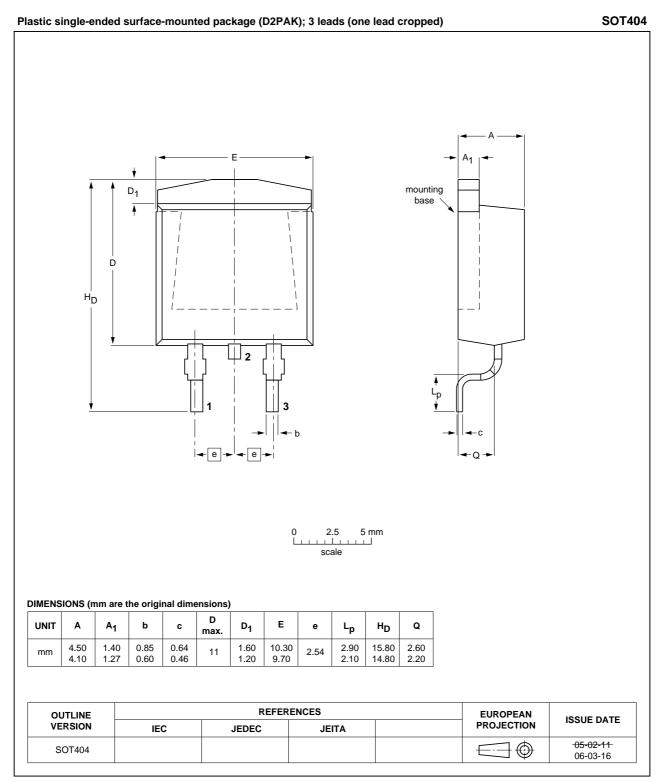


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R7-60BS v.2	20120229	Product data sheet	-	PSMN1R7-60BS v.1
Modifications:	 Status change 	d from objective to product.		
	 Various chang 	es to content.		
PSMN1R7-60BS v.1	20110823	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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